JST139E-800D 16A TRIAC

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D=12V R_L=33	- -	MAX.	5	mA
				10	
V_{GT}		ALL	MAX.	1	V
V_{GD}	V_D=V_{DRM} T_j=125 R_L=3.3k	ALL	MIN.	0.2	V
I_L	I_G=1.2I_{GT}	- -	MAX.	15	mA
				20	
I_H	I_T=500mA		MAX.	10	mA
dV/dt	V_D=540V Gate Open T_j=125		MIN.	40	V s
(dV/dt)c	(dI/dt)c=7.2A/ms, T	54 >>BDC 0.004 Tc 74054 >>BDC 0.004 Tc 800			

FIG.1: Maximum power dissipation versus RMS on-state current

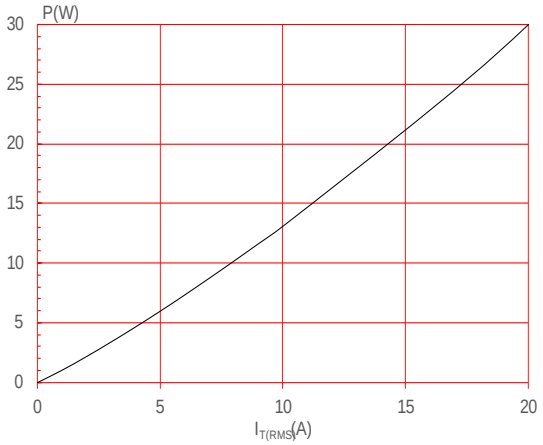
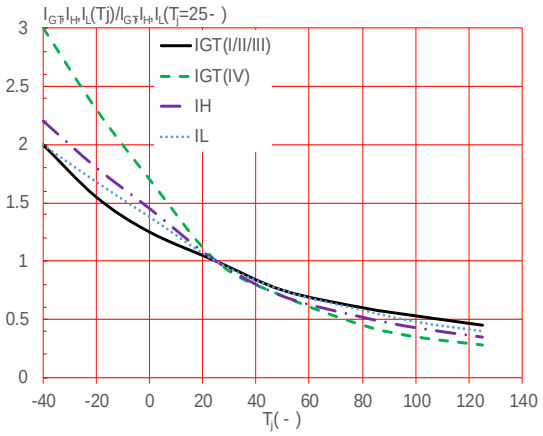


FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		H- I- J	K			
JST139E-800D	800	5	10	TO-263	50	Tube

PACKAGE MECHANICAL DATA

DELIVERY MODE



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